

# PMEG2005CT

# 500 mA low V<sub>F</sub> dual MEGA Schottky barrier rectifier Rev. 01 — 4 June 2009

**Product data sheet** 

## **Product profile**

#### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier in common cathode configuration with an integrated guard ring for stress protection, encapsulated in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features

- Average forward current: I<sub>F(AV)</sub> ≤ 0.5 A
- Reverse voltage: V<sub>R</sub> ≤ 20 V
- Low forward voltage

- AEC-Q101 qualified
- Small SMD plastic package

## 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- High-speed switching
- Low power consumption applications

## 1.4 Quick reference data

Table 1. Quick reference data  $T_i = 25 \,^{\circ}C$  unless otherwise specified.

	· · · · · · · · · · · · · · · · · · ·					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
$I_{F(AV)}$ average forward current		square wave; $\delta = 0.5$ ; f = 20  kHz				
		T <sub>amb</sub> ≤ 100 °C	<u>[1]</u> _	-	0.5	Α
		T <sub>sp</sub> ≤ 130 °C	-	-	0.5	Α
$V_R$	reverse voltage		-	-	20	V
$V_{F}$	forward voltage	$I_F = 0.5 A$	-	360	390	mV
I <sub>R</sub>	reverse current	$V_R = 20 V$	-	30	200	μΑ

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



# 2. Pinning information

Table 2. Pinning

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	anode (diode 1)		
2	anode (diode 2)	3	3
3	common cathode	1 2	1 2 006aab034

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG2005CT	-	plastic surface-mounted package; 3 leads	SOT23

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMEG2005CT	P8*

<sup>[1] \* = -:</sup> made in Hong Kong

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
$V_R$	reverse voltage	$T_j = 25  ^{\circ}C$	-	20	V
I <sub>F(AV)</sub>	average forward current	square wave; $\delta = 0.5$ ; $f = 20 \text{ kHz}$			
		T <sub>amb</sub> ≤ 100 °C	[1] -	0.5	Α
		T <sub>sp</sub> ≤ 130 °C	-	0.5	Α
I <sub>FRM</sub>	repetitive peak forward current	$t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25$	-	3.9	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms	[2] -	10	Α

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<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China



 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device;	one diode loaded				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[3] _	330	mW
			[4] _	400	mW
			[1] -	460	mW
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		<b>–55</b>	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode; d	one diode loaded					
-til(j-a)	thermal resistance from	in free air	<u>[1]</u>			
	junction to ambient		[2] _	-	375	K/W
			[3] _	-	310	K/W
			[4] -	-	270	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[5]</u> _	-	60	K/W

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

<sup>[2]</sup>  $T_i = 25$  °C prior to surge.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[4]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[5]</sup> Soldering point of cathode tab.

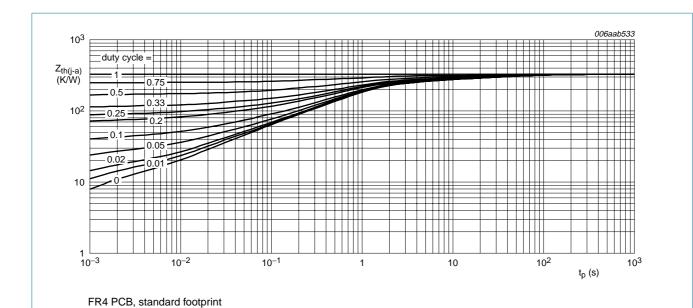


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

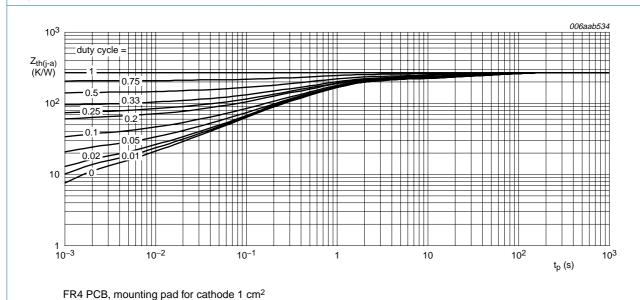
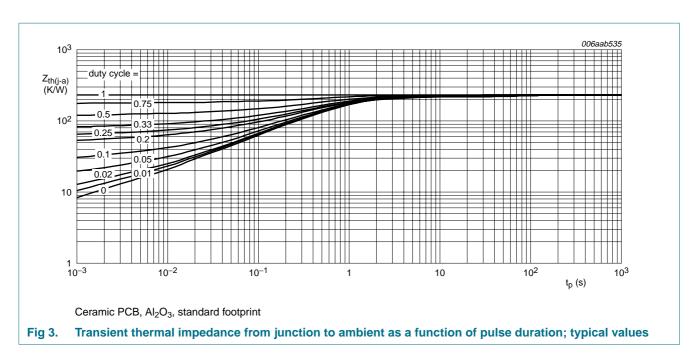


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



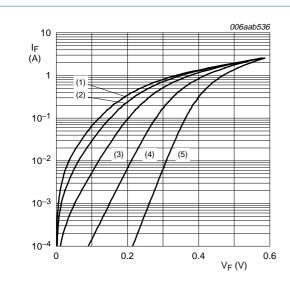
## 7. Characteristics

 Table 7.
 Characteristics

 $T_i = 25 \,^{\circ}C$  unless otherwise specified.

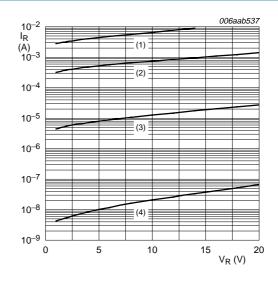
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
V <sub>F</sub>	forward voltage	$I_F = 0.1 \text{ mA}$	-	95	130	mV
		$I_F = 1 \text{ mA}$	-	155	190	mV
		$I_F = 10 \text{ mA}$	-	215	240	mV
		$I_F = 100 \text{ mA}$	-	285	330	mV
		$I_F = 500 \text{ mA}$	-	360	390	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V	-	11	40	μΑ
		V <sub>R</sub> = 20 V	-	30	200	μΑ
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz	-	66	80	pF
t <sub>rr</sub>	reverse recovery time		<u>[1]</u> -	22	-	ns

<sup>[1]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.



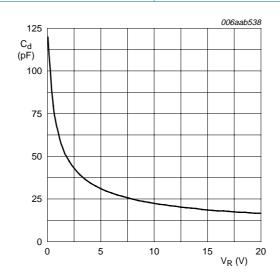
- (1)  $T_i = 150 \,^{\circ}\text{C}$
- (2)  $T_i = 125 \, ^{\circ}C$
- (3)  $T_i = 85 \, ^{\circ}C$
- (4)  $T_j = 25 \, ^{\circ}C$
- (5)  $T_i = -40 \, ^{\circ}C$

Fig 4. Forward current as a function of forward voltage; typical values



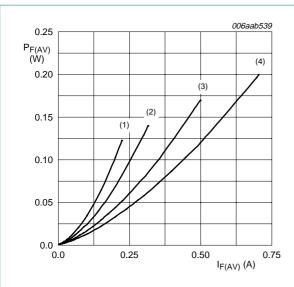
- (1)  $T_j = 125 \, ^{\circ}C$
- (2)  $T_j = 85 \,^{\circ}C$
- (3)  $T_j = 25$  °C
- (4)  $T_j = -40 \, ^{\circ}C$

Fig 5. Reverse current as a function of reverse voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ 

Fig 6. Diode capacitance as a function of reverse voltage; typical values



T<sub>j</sub> = 150 °C

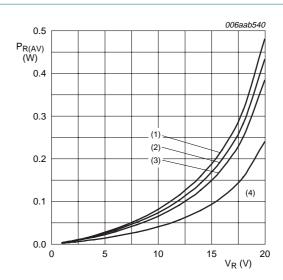
(1)  $\delta = 0.1$ 

(2)  $\delta = 0.2$ 

(3)  $\delta = 0.5$ 

(4)  $\delta = 1$ 

Average forward power dissipation as a Fig 7. function of average forward current; typical values



T<sub>i</sub> = 125 °C

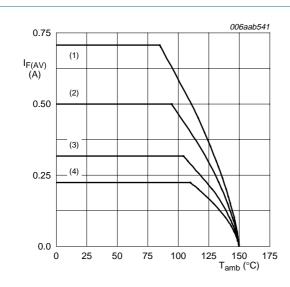
(1)  $\delta = 1$ 

(2)  $\delta = 0.9$ 

(3)  $\delta = 0.8$ 

(4)  $\delta = 0.5$ 

Average reverse power dissipation as a Fig 8. function of reverse voltage; typical values



FR4 PCB, standard footprint

T<sub>i</sub> = 150 °C

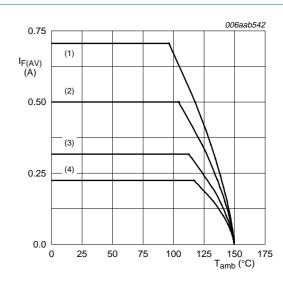
(1)  $\delta = 1$ ; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Average forward current as a function of Fig 9. ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

T<sub>i</sub> = 150 °C

(1)  $\delta = 1$ ; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

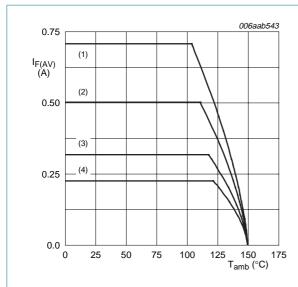
(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values

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#### 500 mA low V<sub>F</sub> dual MEGA Schottky barrier rectifier



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

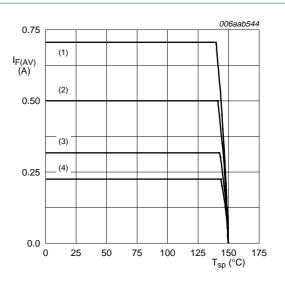
(1)  $\delta = 1$ ; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



T<sub>j</sub> = 150 °C

(1)  $\delta = 1$ ; DC

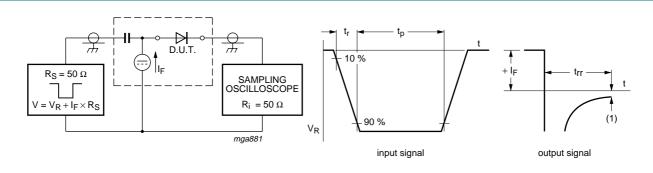
(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 12. Average forward current as a function of solder point temperature; typical values

## 8. Test information



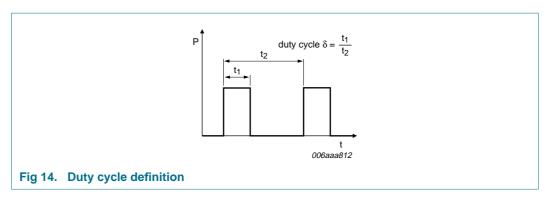
(1)  $I_R = 1 \text{ mA}$ 

Input signal: reverse pulse rise time  $t_r$  = 0.6 ns; reverse voltage pulse duration  $t_p$  = 100 ns; duty cycle  $\delta$  = 0.05 Oscilloscope: rise time  $t_r$  = 0.35 ns

Fig 13. Reverse recovery time test circuit and waveforms

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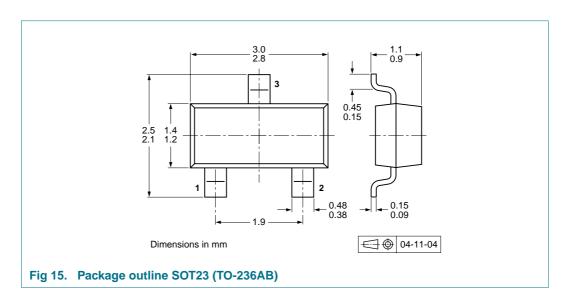
The current ratings for the typical waveforms as shown in <u>Figure 9</u>, <u>10</u>, <u>11</u> and <u>12</u> are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,

 $I_{RMS}=I_{F(AV)}$  at DC, and  $I_{RMS}=I_{M} imes\sqrt{\delta}$  with I<sub>RMS</sub> defined as RMS current.

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Packing information

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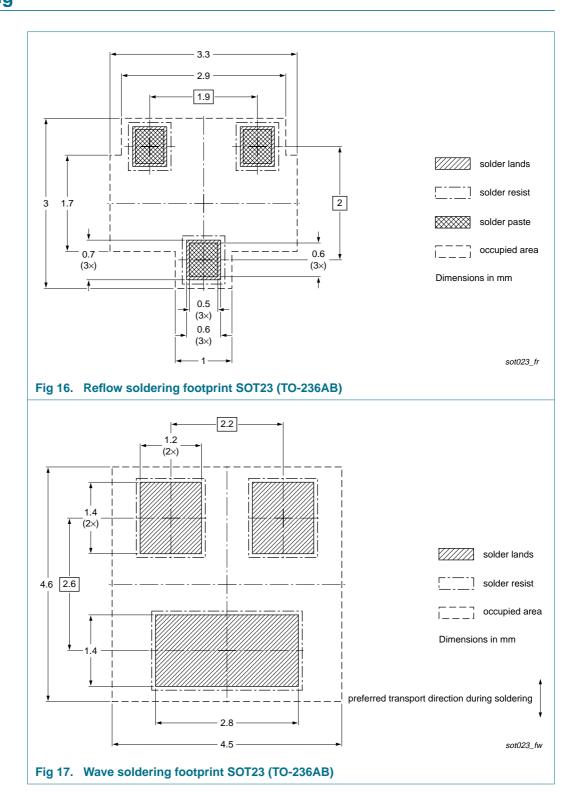
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMEG2005CT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

# 11. Soldering





# 12. Revision history

## Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2005CT_1	20090604	Product data sheet	-	-

# 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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# 500 mA low V<sub>F</sub> dual MEGA Schottky barrier rectifier

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